

# GaN系列紫外探测器 LD-G360-020T

## UVA Sensor: LD-G360-020T

<b>Features</b>	Indium Gallium nitride based material
	Broad band UVA+UVB+UVC photodiode
	Photovoltaic mode operation
	TO-46 metal housing
	Good visible blindness
	High responsivity and low dark current

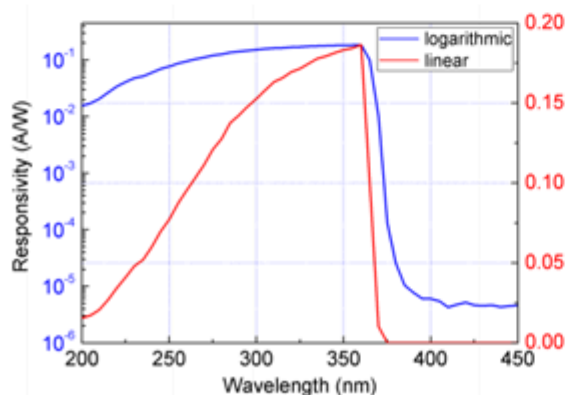


<b>Applications</b>	UV LED monitoring
	UV radiation dose measurement
	UV Curing

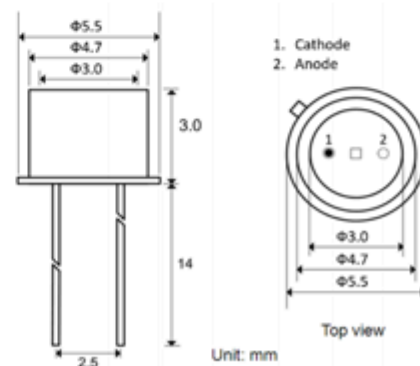
### Specifications

Parameter	Symbol	Value	Unit
<b>Spectral characteristics (25 °C)</b>			
Wavelength of peak responsivity	$\lambda_{\max}$	360	nm
Peak responsivity (at 360 nm)	$R_{\max}$	0.18	A/W
Spectral response range	-	180~370	nm
UV/visible rejection ratio ( $R_{\max}/R_{400\text{ nm}}$ )	VB	$>10^4$	-
<b>General characteristics (25 °C)</b>			
Chip size	A	0.2	mm <sup>2</sup>
Dark current (1 V reverse bias)	$I_d$	<0.1	nA
Capacitance (at 0 V and 1 MHz)	C	4.5	pF
Temperature coefficient	$T_c$	-0.1	%/°C
<b>Maximum ratings</b>			
Operation temperature range	$T_{\text{opt}}$	-40~85	°C
Storage temperature range	$T_{\text{stor}}$	-40~85	°C
Soldering temperature (3 s)	$T_{\text{sold}}$	260	°C
Reverse voltage	$V_{R\max}$	10	V

### Spectral response



### Package dimensions



\*Caution: ESD can damage the device hence please avoid ESD.